

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for pulsed wideband applications operating at frequencies between 3100 and 3500 MHz.

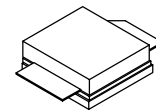
- Typical Pulsed Performance: $V_{DD} = 32$ Volts, $I_{DQ} = 50$ mA,
 $P_{out} = 15$ Watts Peak (3 Watts Avg.), Pulsed Signal, $f = 3500$ MHz,
 Pulse Width = 100 μ sec, Duty Cycle = 20%
 Power Gain — 16 dB
 Drain Efficiency — 41%
- Typical WiMAX Performance: $V_{DD} = 32$ Volts, $I_{DQ} = 150$ mA,
 $P_{out} = 1.8$ Watts Avg., $f = 3500$ MHz, 802.16d, 64 QAM $3/4$, 4 Bursts,
 10 MHz Channel Bandwidth, Input Signal PAR = 9.5 dB @ 0.01%
 Probability on CCDF
 Power Gain — 18 dB
 Drain Efficiency — 16%
 RCE — -33 dB (EVM — 2.2% rms)
- Capable of Handling 10:1 VSWR, @ 32 Vdc, 3300 MHz, 15 Watts Peak Power
- Capable of Handling 3 dB Overdrive @ 32 Vdc

Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 32 mm, 13 inch Reel.

MRF7S35015HSR3

**3100-3500 MHz, 15 W PEAK, 32 V
 PULSED
 LATERAL N-CHANNEL
 RF POWER MOSFET**



**CASE 465J-02, STYLE 1
 NI-400S-240**

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Operating Voltage	V_{DD}	32, +0	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	$^{\circ}$ C
Case Operating Temperature	T_C	150	$^{\circ}$ C
Operating Junction Temperature (1,2)	T_J	225	$^{\circ}$ C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 80 $^{\circ}$ C, 15 W Pulsed, 100 μ sec Pulse Width, 20% Duty Cycle Case Temperature 81 $^{\circ}$ C, 15 W Pulsed, 500 μ sec Pulse Width, 10% Duty Cycle	$R_{\theta JC}$	0.60 0.73	$^{\circ}$ C/W

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

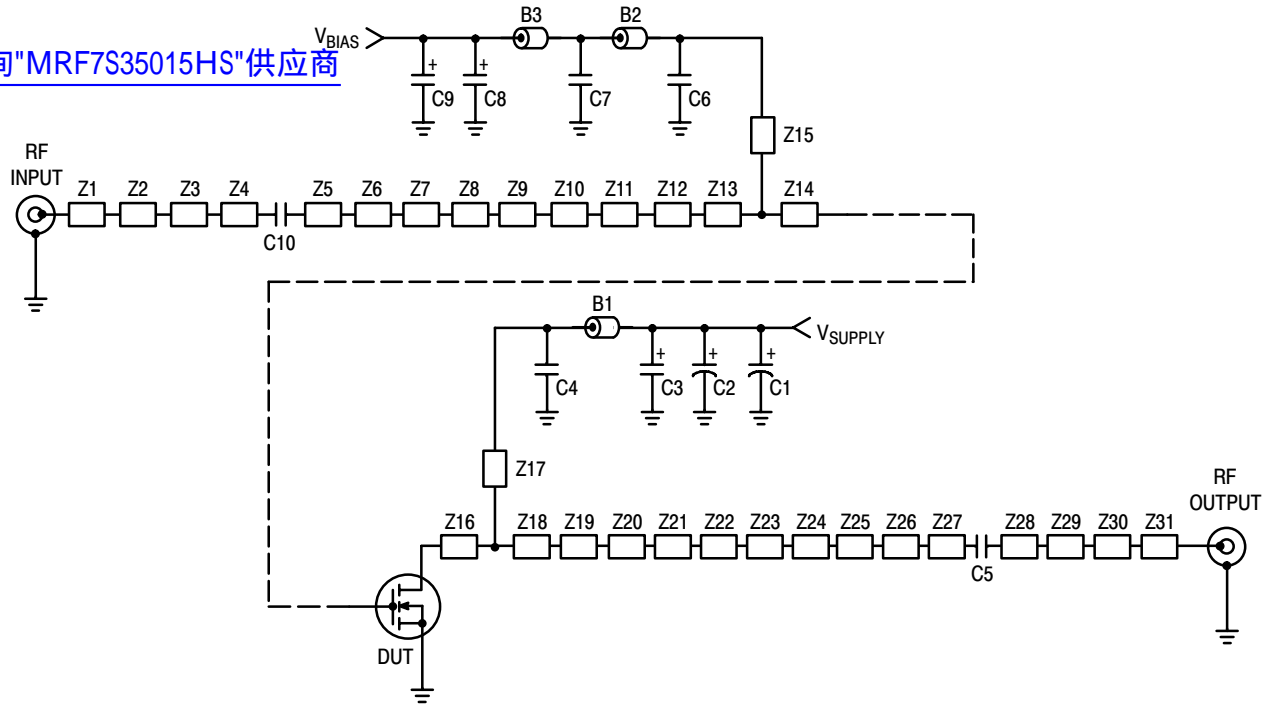
Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1B (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 32\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	2	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
On Characteristics					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 33.5\ \mu\text{Adc}$)	$V_{GS(th)}$	1.2	2	2.7	Vdc
Gate Quiescent Voltage ($V_{DD} = 32\text{ Vdc}$, $I_D = 50\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	1.8	2.5	3.3	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 300\text{ mAdc}$)	$V_{DS(on)}$	0.1	1.7	0.3	Vdc
Dynamic Characteristics (1)					
Reverse Transfer Capacitance ($V_{DS} = 32\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	0.12	—	pF
Output Capacitance ($V_{DS} = 32\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	92	—	pF
Input Capacitance ($V_{DS} = 32\text{ Vdc}$, $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)	C_{iss}	—	46	—	pF
Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 32\text{ Vdc}$, $I_{DQ} = 50\text{ mA}$, $P_{out} = 15\text{ W Peak}$ (3 W Avg.), $f = 3100\text{ MHz}$ and $f = 3500\text{ MHz}$, Pulsed, 100 μsec Pulse Width, 20% Duty Cycle, 25 ns Input Rise Time					
Power Gain	G_{ps}	13	16	19	dB
Drain Efficiency	η_D	38	41	—	%
Input Return Loss	IRL	—	-12	-7	dB
Pulsed RF Performance (In Freescale Application Test Fixture, 50 ohm system) $V_{DD} = 32\text{ Vdc}$, $I_{DQ} = 50\text{ mA}$, $P_{out} = 15\text{ W Peak}$ (3 W Avg.), $f = 3100\text{ MHz}$ and $f = 3500\text{ MHz}$, Pulsed, 100 μsec Pulse Width, 20% Duty Cycle, 25 ns Input Rise Time					
Output Pulse Droop (500 μsec Pulse Width, 10% Duty Cycle)	DRP_{out}	—	0.2	—	dB
Load Mismatch Tolerance (VSWR = 10:1 at all Phase Angles)	VSWR-T	No Degradation in Output Power			

1. Part internally matched both on input and output.



Z1	0.375" x 0.071" Microstrip	Z18	0.078" x 0.454" Microstrip
Z2*	0.126" x 0.524" Microstrip	Z19	0.055" x 0.244" Microstrip
Z3*	0.079" x 0.016" Microstrip	Z20	0.630" x 0.073" Microstrip
Z4	0.153" x 0.071" Microstrip	Z21	0.218" x 0.038" Microstrip
Z5	0.076" x 0.520" Microstrip	Z22	0.060" x 0.552" Microstrip
Z6	0.037" x 0.252" Microstrip	Z23	0.079" x 0.038" Microstrip
Z7	0.084" x 0.73" Microstrip	Z24	0.062" x 0.526" Microstrip
Z8	0.123" x 0.440" Microstrip	Z25	0.032" x 0.070" Microstrip
Z9	0.048" x 0.073" Microstrip	Z26	0.110" x 0.526" Microstrip
Z10	0.081" x 0.184" Microstrip	Z27	0.053" x 0.072" Microstrip
Z11	0.030" x 0.262" Microstrip	Z28	0.028" x 0.070" Microstrip
Z12	0.525" x 0.336" Microstrip	Z29	0.098" x 0.148" Microstrip
Z13	0.182" x 0.466" Microstrip	Z30	0.062" x 0.526" Microstrip
Z14	0.077" x 0.466" Microstrip	Z31	0.529" x 0.070" Microstrip
Z15	0.603" x 0.048" Microstrip	PCB	Arlon CuClad 250GX-0300-55-22, 0.030", $\epsilon_r = 2.55$
Z16	0.063" x 0.618" Microstrip		
Z17	0.534" x 0.040" Microstrip		

* Line length includes microstrip bends

Figure 1. MRF7S35015HSR3 Test Circuit Schematic

Table 5. MRF7S35015HSR3 Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1*	Long Ferrite Bead	2743021447	Fair-Rite
B2, B3	Short Ferrite Beads	2743019447	Fair-Rite
C1	470 μ F, 63 V Electrolytic Capacitor	477KXM063M	Illinois Cap
C2	47 μ F, 50 V Electrolytic Capacitor	476KXM050M	Illinois Cap
C3, C9	22 μ F, 35 V Tantalum Capacitors	T491X226K035AT	Kemet
C4, C5, C10	2.7 pF Chip Capacitors	ATC100B2R7BT500XT	ATC
C6	0.8 pF Chip Capacitor	ATC100B0R8BT500XT	ATC
C7	0.1 μ F Chip Capacitor	CDR33BX104AKYS	AVX
C8	22 μ F, 25 V Tantalum Capacitor	T491D226K025AT	Kemet

*B1 is removed for WiMAX circuit performance.

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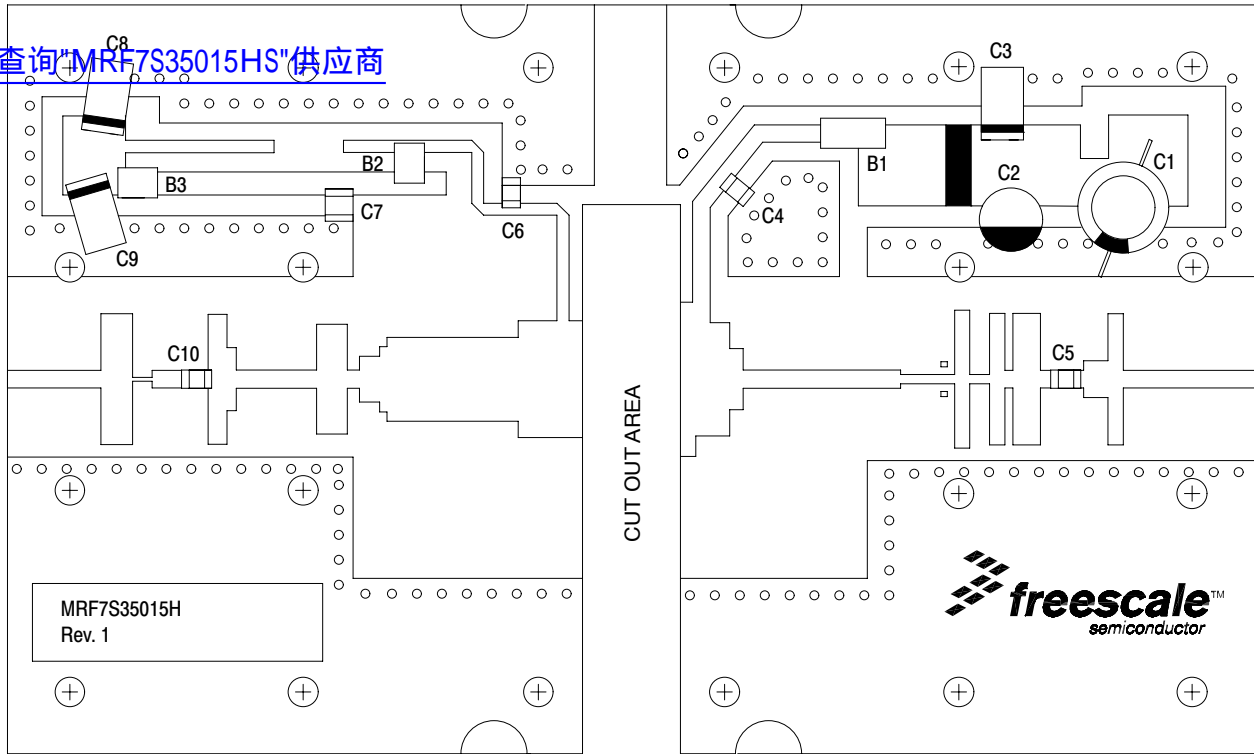


Figure 2. MRF7S35015HSR3 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

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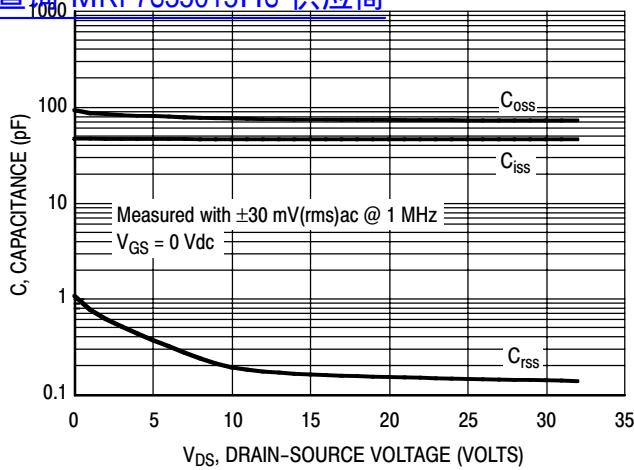


Figure 3. Capacitance versus Drain-Source Voltage

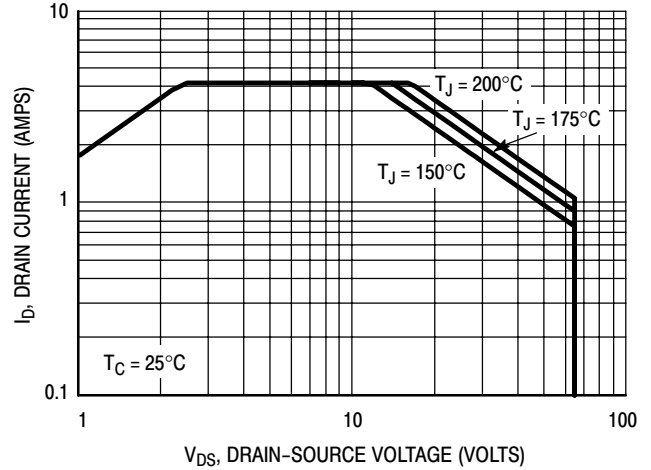


Figure 4. DC Safe Operating Area

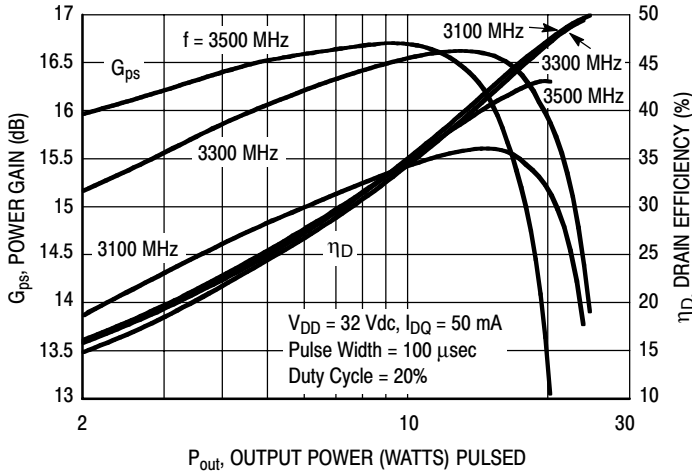


Figure 5. Pulsed Power Gain and Drain Efficiency versus Output Power

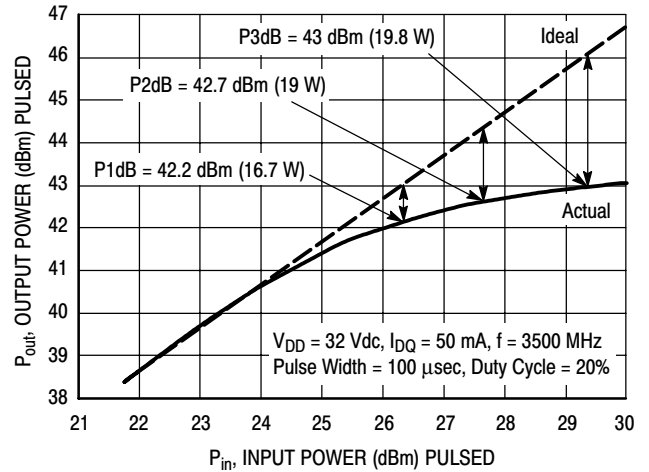


Figure 6. Pulsed Output Power versus Input Power

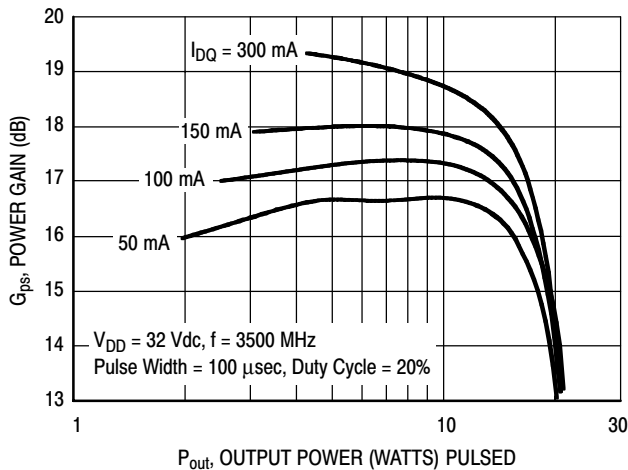


Figure 7. Pulsed Power Gain versus Output Power

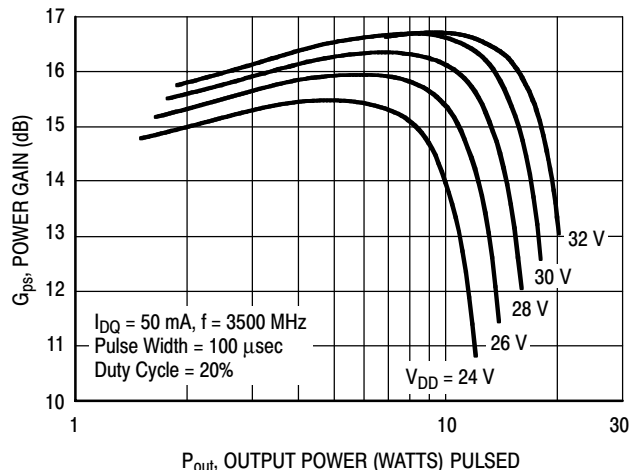


Figure 8. Pulsed Power Gain versus Output Power

MRF7S35015HSR3

TYPICAL CHARACTERISTICS

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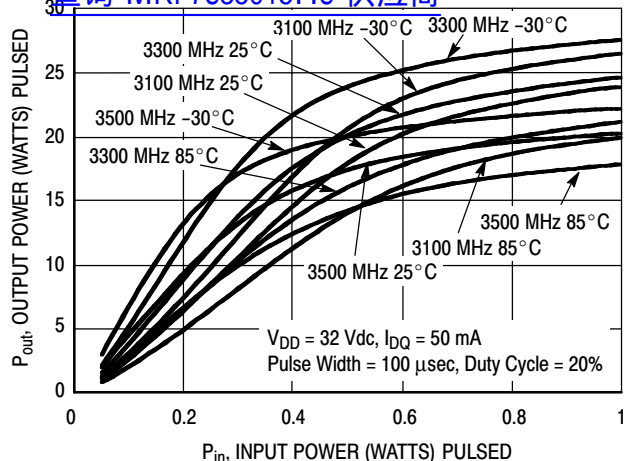


Figure 9. Pulsed Output Power versus Input Power

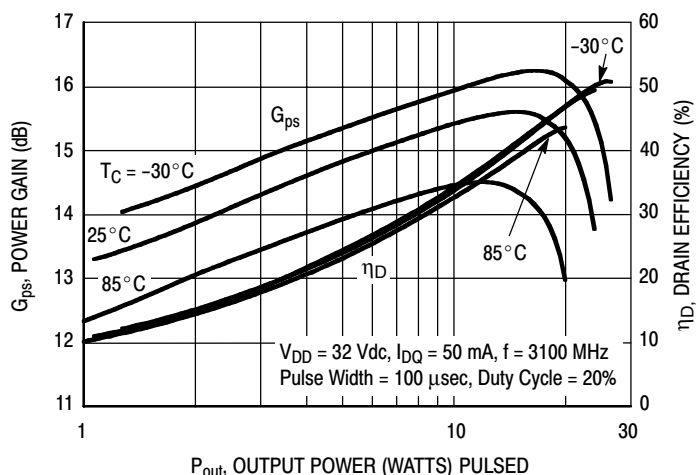


Figure 10. Pulsed Power Gain and Drain Efficiency versus Output Power — 3100 MHz

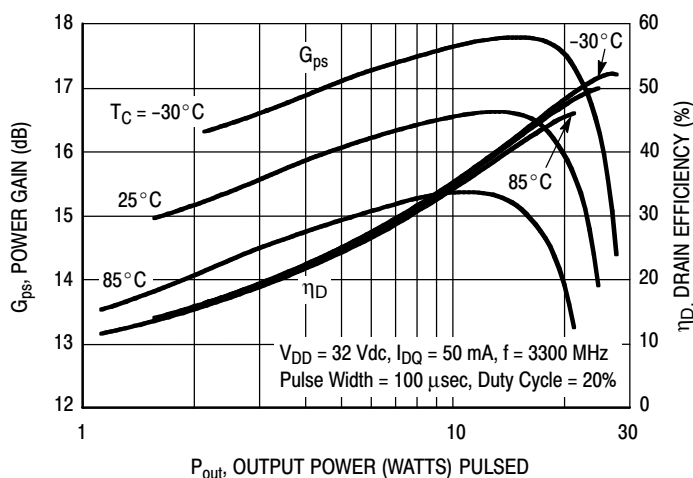


Figure 11. Pulsed Power Gain and Drain Efficiency versus Output Power — 3300 MHz

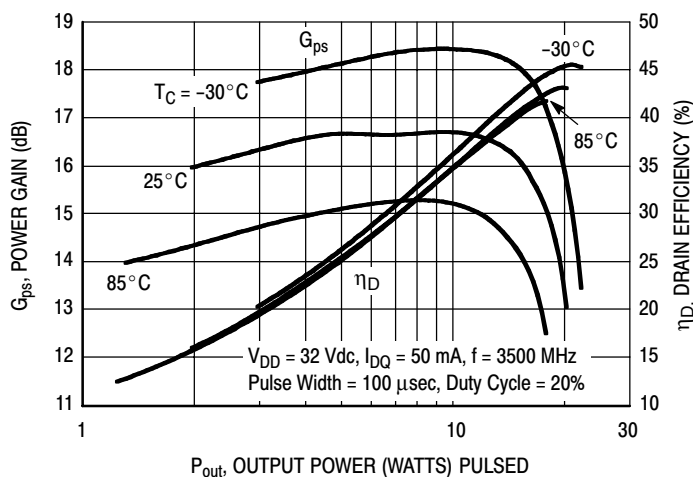


Figure 12. Pulsed Power Gain and Drain Efficiency versus Output Power — 3500 MHz

TYPICAL CHARACTERISTICS

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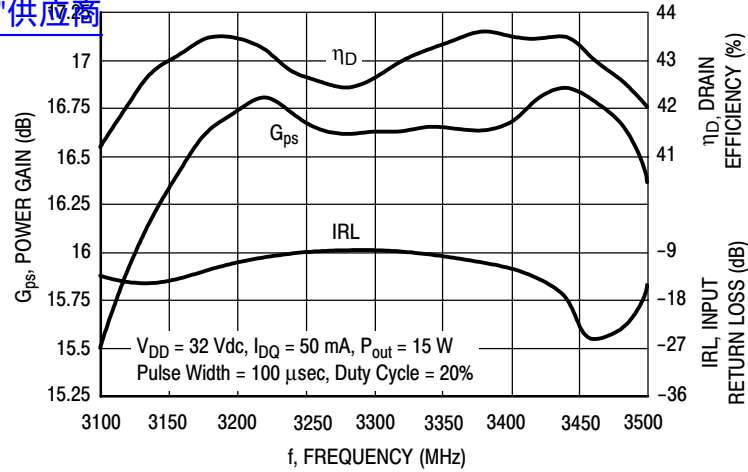


Figure 13. Pulsed Power Gain, Drain Efficiency and IRL versus Frequency

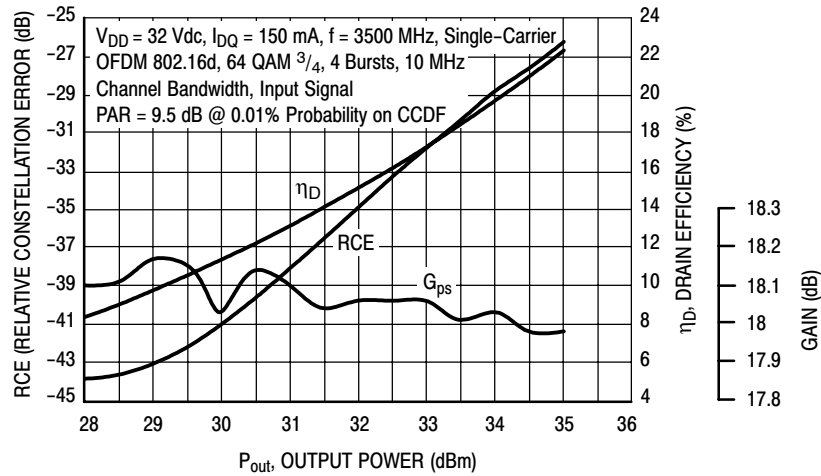
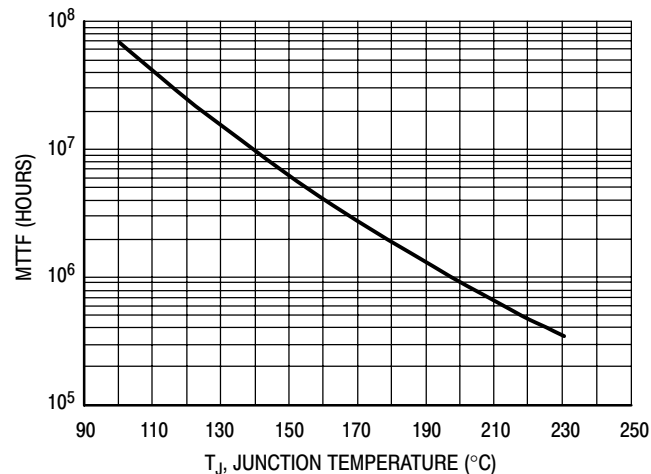


Figure 14. Single-Channel OFDM Relative Constellation Error, Drain Efficiency and Gain versus Output Power

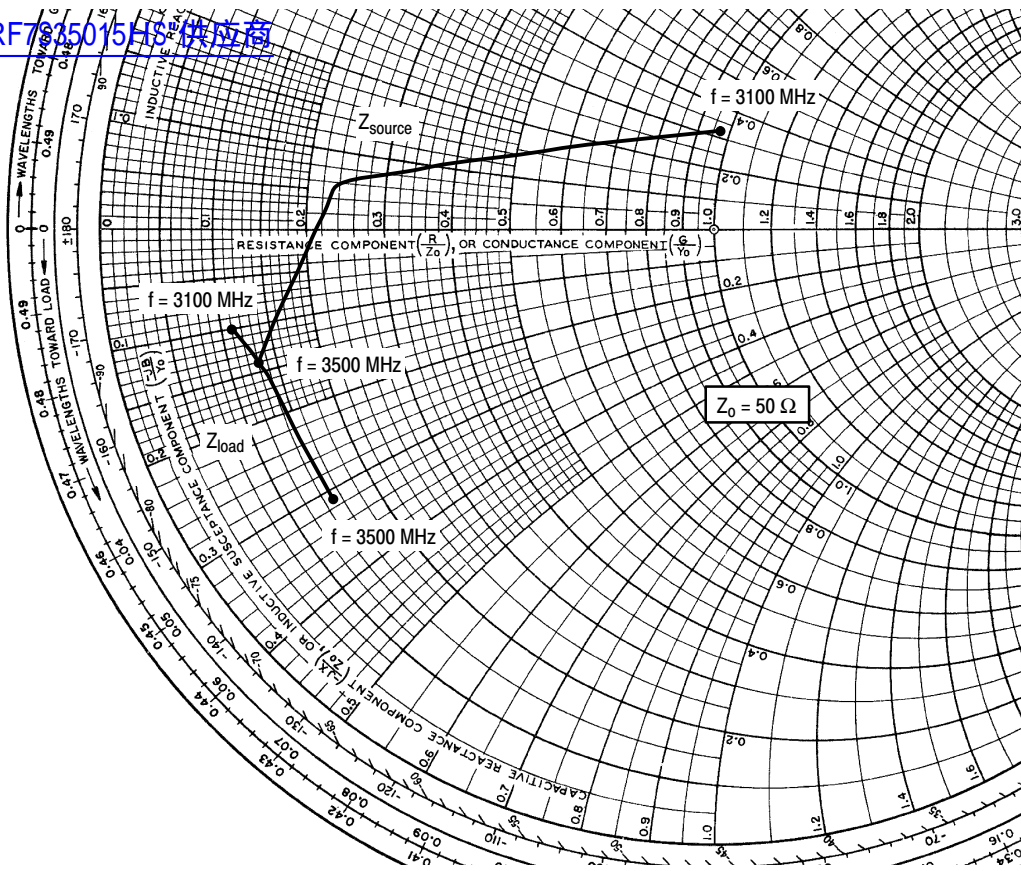


This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 32$ Vdc, $P_{out} = 15$ W Peak, Pulse Width = 100 μ sec, Duty Cycle = 20%, and $\eta_D = 41\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 15. MTTF versus Junction Temperature

MRF7S35015HSR3



$V_{DD} = 32 \text{ Vdc}$, $I_{DQ} = 50 \text{ mA}$, $P_{out} = 15 \text{ W Peak}$

f MHz	Z_{source} Ω	Z_{load} Ω
3100	$48.6 + j16.1$	$5.6 - j5.2$
3300	$11.8 + j3.15$	$6.36 - j6.83$
3500	$6.43 - j6.79$	$7.41 - j15.5$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

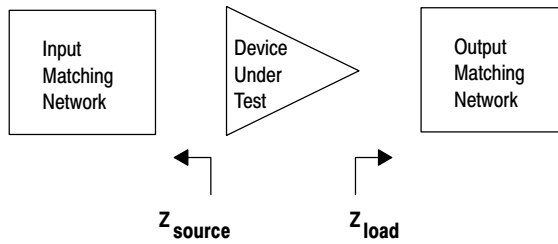
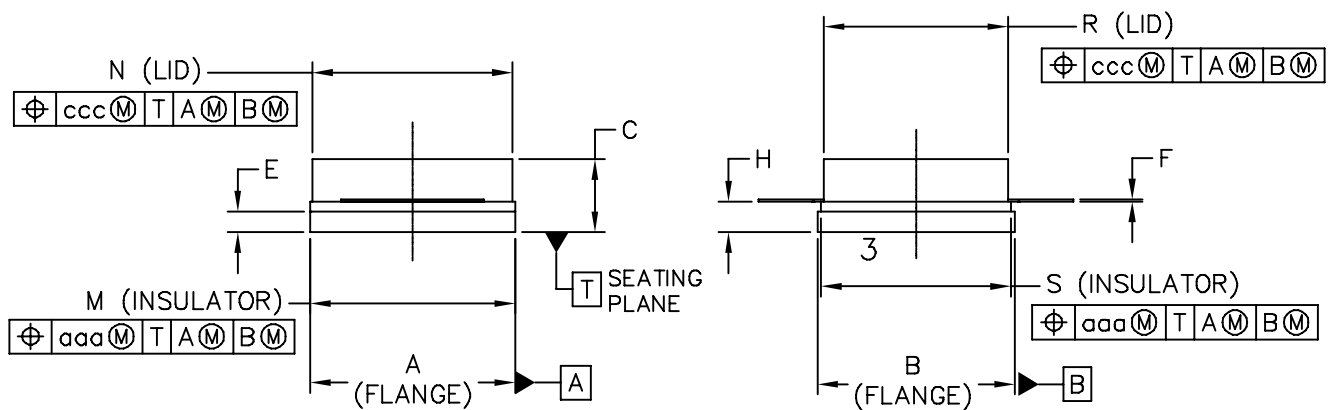
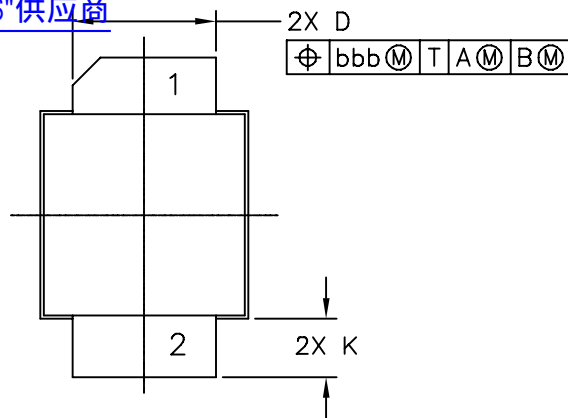


Figure 16. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS

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	CASE NUMBER: 465J-02	09 MAY 2006	
	STANDARD: NON-JEDEC		

MRF7S35015HSR3

NOTES:

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2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DIMENSION H IS MEASURED .030 (0.762) AWAY FROM PACKAGE BODY

STYLE 1:

- PIN 1 - DRAIN
- 2 - GATE
- 3 - SOURCE

STYLE 2:

- PIN 1 - GATE
- 2 - DRAIN
- 3 - SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.395	.405	10.03	10.29	aaa	.005		0.127	
B	.380	.390	9.65	9.91	bbb	.010		0.254	
C	.125	.163	3.18	4.14	ccc	.015		0.381	
D	.275	.285	6.98	7.24					
E	.035	.045	0.89	1.14					
F	.004	.006	0.10	0.15					
H	.057	.067	1.45	1.70					
K	.0995	.1295	2.53	3.29					
M	.395	.405	10.03	10.29					
N	.385	.395	9.78	10.03					
R	.355	.365	9.02	9.27					
S	.365	.375	9.27	9.53					
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					CASE NUMBER: 465J-02			09 MAY 2006	
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PRODUCT DOCUMENTATION

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Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	June 2008	• Initial Release of Data Sheet
1	Aug. 2008	• Added p. 1 of Case 465J-02 Mechanical Outline drawing, p. 9

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